## 2SD1499

## Silicon NPN triple diffusion planar type

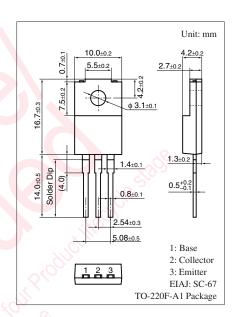
For high power amplification Complementary to 2SB1063

#### ■ Features

- Extremely satisfactory linearity of the forward current transfer ratio h<sub>FE</sub>
- Wide safe operation area
- High transition frequency f<sub>T</sub>
- Full-pack package which can be installed to the heat sink with one screw.

### ■ Absolute Maximum Ratings $T_C = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	100	V	
Collector-emitter voltage (Base open)	$V_{CEO}$	100	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Collector current	$I_{C}$	5	A	
Peak collector current	$I_{CP}$	8	A	
Collector power	P <sub>C</sub>	40	W	
dissipation $T_a = 25$ °C		2.0	101	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C C	



### ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

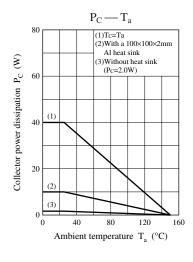
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Base-emitter voltage	$V_{BE}$	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ A}$		0.	1.8	V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 100 \text{ V}, I_E = 0$	160		50	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 3 \text{ V}, I_{C} = 0$			50	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$	20			_
	h <sub>FE2</sub> *	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$	40		200	
	h <sub>FE3</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ A}$	20			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 0.3 \text{ A}$			2.0	V
Transition frequency	$f_T$	$V_{CE} = 5 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		90		pF
(Common base, input open circuited)		,				

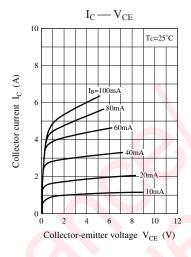
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

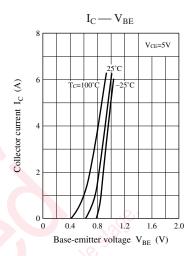
#### 2. \*: Rank classification

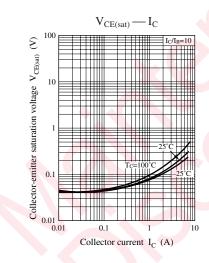
Rank	R	Q	Р
h <sub>FE2</sub>	40 to 80	60 to120	100 to 200

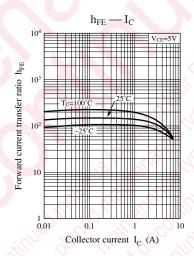
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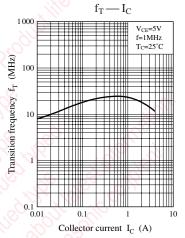


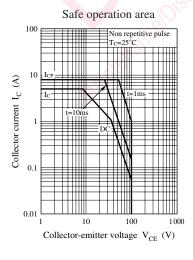


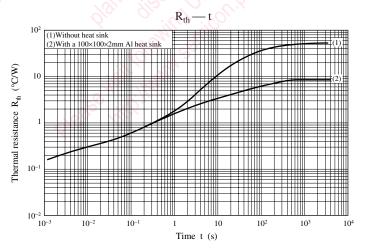












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